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U.S. PATENT DOCUMENTS

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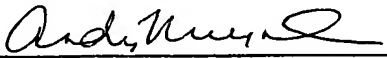
FOREIGN PATENT DOCUMENTS

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

ah	C01	W.J. Ho, M.F. Chang, S.M. Beccue, P.J. Zampardi, J. Yu, A. Sailer, R.L. Pierson, K.C. Wang, "A GaAs BiFET LSI technology", GaAs IC Sym. Tech. Dig., 1994, p.47.
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ah	C06	Y. F. Yang, C.C. Hsu, E.S. Yang, "Integration of GaInP/GaAs heterojunction bipolar transistors and high electron mobility transistors", IEEE Electron Device Lett., vol. 17, no. 7, July 1996, p. 363
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ah	C08	J. Jang, E. C. Kan, T. Arnborg, T. Johansson, R. Dutton, "Characterization of RF Power BJT and Improvement of Thermal Stability with Nonlinear Base Ballasting", 1998 IEE, pg. 1428.

Examiner.		Date Considered	07/19/05
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